



Solid State Devices, Inc.

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SFT2805

-30 mA, -25 V Dual PNP Transistor

DESIGNER'S DATA SHEET

Part Number / Ordering Information ^{1/}

SFT2805 $\overline{\square}$ Screening ^{2/} $\underline{\quad}$ = Not Screened
TX = TX Level
TXV = TXV Level
S = S Level

Features:

- Hermetically Sealed Package
- Replacement for 2N2805
- Complementary Use with 2N2639 – 2N2644 Dual NPN Transistors
- TX, TXV, S-Level Screening Available - Consult Factory

Maximum Ratings	Symbol	Each Triode	Total Device	Units
Collector – Base Voltage	V_{CB0}	-25	-	V
Collector – Emitter Voltage ^{3/}	V_{CE0}	-20	-	V
Emitter – Base Voltage	V_{EB0}	-5	-	V
Continuous Collector Current	I_C	-30	-	mA
Continuous Device Dissipation @ $T_A = 25^\circ C$ ^{4/} Continuous Device Dissipation @ $T_C = 25^\circ C$ ^{5/}	P_D	0.25 0.5	0.5 1	W
Storage Temperature Range	T_J & T_{STG}	-65 to +200		$^\circ C$
Lead Temperature 1/16 inch from Case for 10 Seconds		230 $^\circ C$		$^\circ C/W$

NOTES:

*Pulse Test: Pulse Width = 300 μ sec, Duty Cycle < 2%

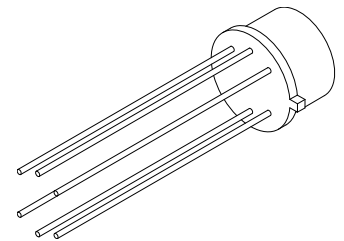
1/ For ordering information, price, and availability, contact factory.

2/ Screening based on MIL-PRF-19500. Screening flows available on request.

3/ This value applies when the base-emitter diode is open-circuited.

4/ For each triode derate linearly to 175 $^\circ C$ free-air temperature at the rate of 1.67 mW/ $^\circ C$.

5/ For each triode derate linearly to 175 $^\circ C$ case temperature at the rate of 3.33 mW/ $^\circ C$.





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Individual Triode Characteristics ^{6/7/}		Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage ^{8/}	$I_C = -10 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	-20	—	V
Collector Cutoff Current	$V_{CB} = -25 \text{ V}, I_E = 0$ $V_{CB} = -25 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$	I_{CB01}	—	-10	nA
		I_{CB02}	—	-10	μA
Emitter Cutoff Current	$V_{EB} = -5 \text{ V}, I_C = 0$	I_{EBO}	—	-10	nA
Static Forward Current Transfer Ratio	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}, T_A = -55^\circ\text{C}$ $V_{CE} = -5 \text{ V}, I_C = -10 \mu\text{A}$ $V_{CE} = -5 \text{ V}, I_C = -1 \text{ mA}$	h_{FE1}	30	—	
		h_{FE2}	40	120	
		h_{FE3}	20	—	
		h_{FE4}	40	—	
Base-Emitter Voltage	$I_B = -1 \text{ mA}, I_C = -10 \text{ mA}$	V_{BE}	-0.7	-0.9	V
Collector-Emitter Saturation Voltage	$I_B = -1 \text{ mA}, I_C = -10 \text{ mA}$	$V_{CE(SAT)}$	—	-0.5	V
Small-Signal Common-Base Input Impedance	$V_{CB} = -5 \text{ V}, I_E = 1 \text{ mA}, f = 1 \text{ kHz}$	h_{ib}	25	32	Ω
Small-Signal Common-Base Reverse Voltage Transfer Ratio		h_{rb}		12×10^{-4}	
Small-Signal Common-Base Output Admittance		h_{ob}		1	μmho
Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = -5 \text{ V}, I_C = -1 \text{ mA}, f = 1 \text{ kHz}$	h_{fe}	40	200	
Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = -5 \text{ V}, I_C = -1 \text{ mA}, f = 20 \text{ MHz}$	$ h_{fe} $	3	—	
Common-Base Open-Circuit Output Capacitance	$V_{CB} = -5 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	C_{obo}	—	8	pF

Triode Matching Characteristics ^{7/}		Symbol	Min	Max	Units
Static Forward-Current-Gain Balance Ratio	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}^{10/}$	$\frac{h_{FE1}}{h_{FE2}}$	0.9	1	
Base-Emitter-Voltage Differential	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}$	$ V_{BE1} - V_{BE2} $	—	5	mV
Base-Emitter-Voltage-Differential Temperature Gradient	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}, \Delta T_A = [25^\circ\text{C} - (-55^\circ\text{C})] \text{ and } [125^\circ\text{C} - 25^\circ\text{C}]$	$\frac{\Delta(V_{BE1} - V_{BE2})}{\Delta T_A}$	—	10	$\mu\text{V}/^\circ\text{C}$

Individual Triode Characteristics ^{9/1/}		Symbol	Max	Units
Average Noise Figure	$V_{CB} = -5 \text{ V}, I_E = 10 \mu\text{A}, R_G = 10 \text{ k}\Omega,$ Noise Bandwidth = 15.7 kHz ^{11/}	\bar{F}	—	V

NOTES:

6/ The terminals of the triode not under test are open-circuited for the measurement of these characteristics.

7/ Electrical characteristics at 25°C free-air temperature (unless otherwise noted).

8/ This parameter must be measured using pulse techniques. $t_w = 300 \mu\text{s}$, duty cycle < 2%.

9/ Operating characteristics at 25°C free-air temperature.

10/ The lower of the two h_{FE} readings is taken as h_{FE1} .

11/ Average Noise Figure is measured in an amplifier with low-frequency response down 3 dB at 10 Hz and 10 kHz and a high-frequency roll off, of 6 dB/octave.

12/ Contact factory for case outlines.

NOTE: All specifications are subject to change without notification.
 SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0139A

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